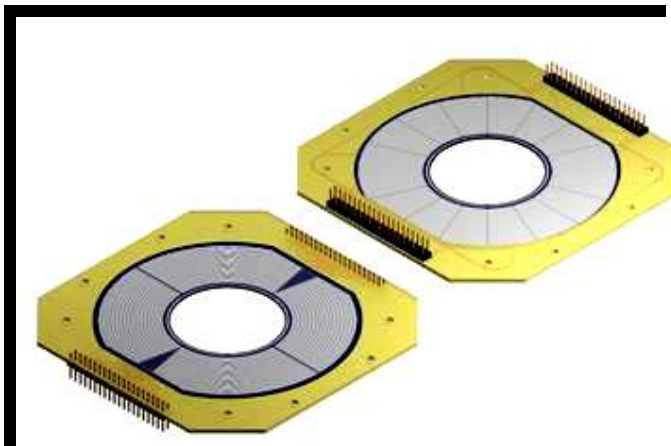


SPECIALIST DETECTORS FOR NUCLEAR PHYSICS

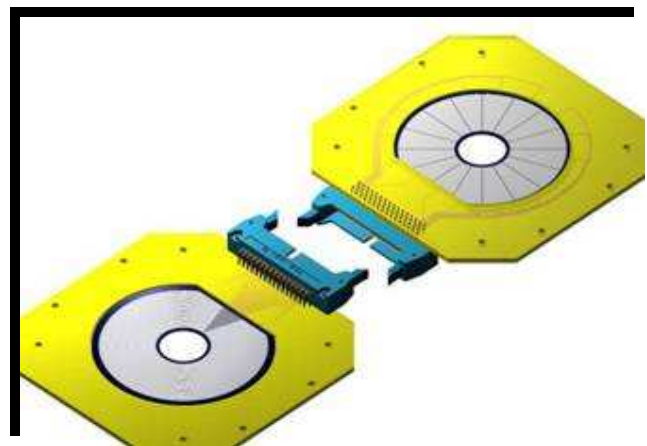
SILICON DETECTOR TYPE: SINGLE AND DOUBLE SIDED RING COUNTER DESIGN

DESIGN: Silicon planar ion implanted passivated structure p on n silicon totally depleted single sided multi ring with 90° segments with optional double sided segments of 22.5° exhibiting over voltage capability with excellent radiation damage resistance and annealing capability for high neutron and heavy ion damage.

DESIGN	S1	S2
TECHNOLOGY	4	4
ACTIVE AREA	53 cm ²	35 cm ²
ACTIVE OUTER DIAMETER	96 mm	70 mm
ACTIVE INNER DIAMETER	48 mm	22 mm
ANNULAR HOLE DIAMETER	46 mm	20 mm
N ^o of FRONT SEGMENTS	4	
N ^o of FRONT CONTACT PADS	64	48
N ^o of BACK SEGMENTS	16	16
N ^o of BACK CONTACT PADS	16	16



S1 detector and PCB as viewed from the p- and n-side.



S2 detector and PCB as viewed from the p- and n-side

DETECTOR THICKNESS RANGE:

- S1 65 μm, 140 μm, 300 μm and 500 μm
- S2 65 μm, 140 μm, 300 μm, 500 μm and 1000 μm

PACKAGE: PCB, ceramic or PCB Kapton subject to design
 READOUT: 100 % on both sides
 CONTACTS METALLISATION: Aluminum front 1000 Å, back gold 3000 Å

QUALITY ASSURANCE :ISO9001

